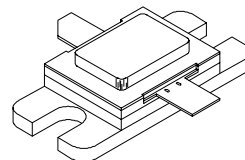


RF & MICROWAVE TRANSISTORS AVIONICS APPLICATIONS

- DESIGNED FOR HIGH POWER PULSED IFF
- 600 WATTS (min.) IFF 1030 or 1090 MHz
- REFRACTORY GOLD METALLIZATION
- 6.0 dB MIN. GAIN
- LOW THERMAL RESISTANCE FOR RELIABILITY AND RUGGEDNESS
- 30:1 LOAD VSWR CAPABILITY AT SPECIFIED OPERATING CONDITIONS
- INPUT MATCHED, COMMON BASE CONFIGURATION



.400 x .500 2LFL (M112)
hermetically sealed

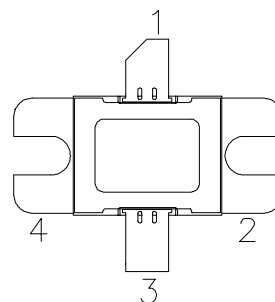
ORDER CODE
SD1542-42

BRANDING
SD1542-42

DESCRIPTION

The SD1542-42 is a hermetically sealed, gold metallized, silicon NPN power transistor. The SD1542-42 is designed for applications requiring high peak power and low duty cycles such as IFF. The SD1542-42 is packaged in a hermetic metal/ceramic package with internal input matching, resulting in improved broadband performance and low thermal resistance.

PIN CONNECTION



1. Collector	3. Emitter
2. Base	4. Base

ABSOLUTE MAXIMUM RATINGS ($T_{case} = 25^{\circ}C$)

Symbol	Parameter	Value	Unit
V_{CC}	Collector-Supply Voltage*	55	V
I_C	Device Current* ($T_C \leq 100^{\circ}C$)	45	A
P_{DISS}	Power Dissipation*	1670	W
T_J	Junction Temperature	+200	$^{\circ}C$
T_{STG}	Storage Temperature	- 65 to +200	$^{\circ}C$

THERMAL DATA

$R_{TH(j-c)}$	Junction-Case Thermal Resistance*	0.06	$^{\circ}C/W$
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* Applies only to rated RF operation.

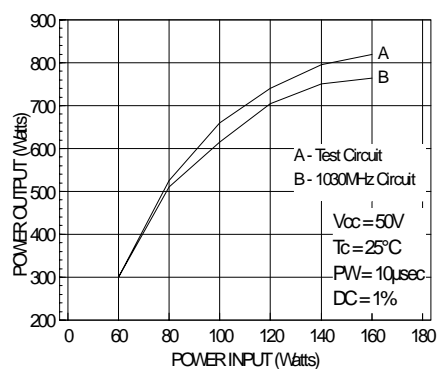
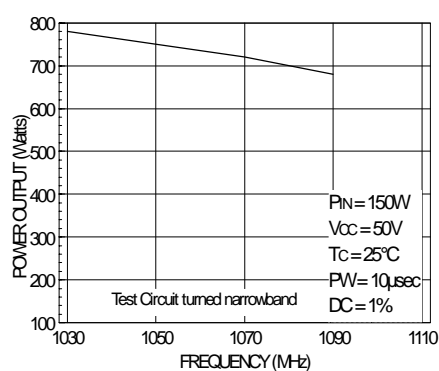
ELECTRICAL SPECIFICATIONS ($T_{\text{case}} = 25^{\circ}\text{C}$)**STATIC**

Symbol	Test Conditions		Value			Unit
			Min.	Typ.	Max.	
BV_{CBO}	$I_{\text{C}} = 25 \text{ mA}$	$I_{\text{E}} = 0 \text{ mA}$	65	—	—	V
BV_{CER}	$I_{\text{C}} = 25 \text{ mA}$	$R_{\text{BE}} = 10 \Omega$	65	—	—	V
BV_{EBO}	$I_{\text{E}} = 10 \text{ mA}$	$I_{\text{C}} = 0 \text{ mA}$	3.5	—	—	V
I_{CES}	$V_{\text{CE}} = 50 \text{ V}$	$V_{\text{BE}} = 0 \text{ V}$	—	—	60	mA
h_{FE}	$V_{\text{CE}} = 5 \text{ V}$	$I_{\text{C}} = 2 \text{ A}$	10	—	250	—

DYNAMIC

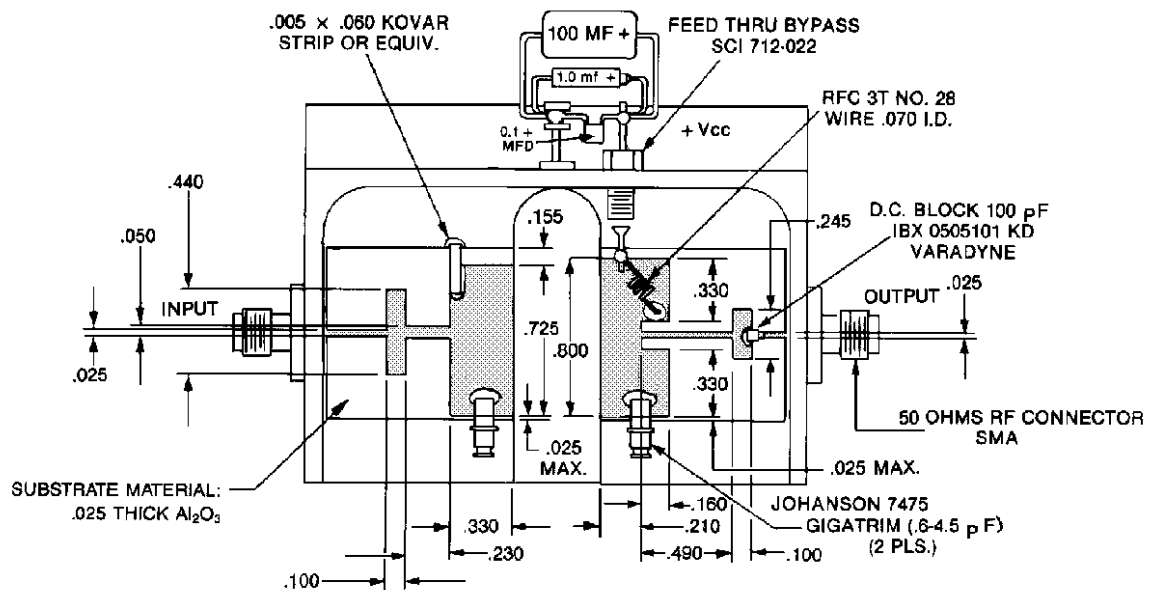
Symbol	Test Conditions			Value			Unit
				Min.	Typ.	Max.	
P_{OUT}	$f = 1090 \text{ MHz}$	$P_{\text{IN}} = 150 \text{ W}$	$V_{\text{CC}} = 50 \text{ V}$	600	680	—	W
η_{C}	$f = 1090 \text{ MHz}$	$P_{\text{IN}} = 150 \text{ W}$	$V_{\text{CC}} = 50 \text{ V}$	35	40	—	%
G_{P}	$f = 1090 \text{ MHz}$	$P_{\text{IN}} = 150 \text{ W}$	$V_{\text{CC}} = 50 \text{ V}$	6.0	6.6	—	dB

Note: Pulse Width = 10 μ Sec, Duty Cycle = 1%

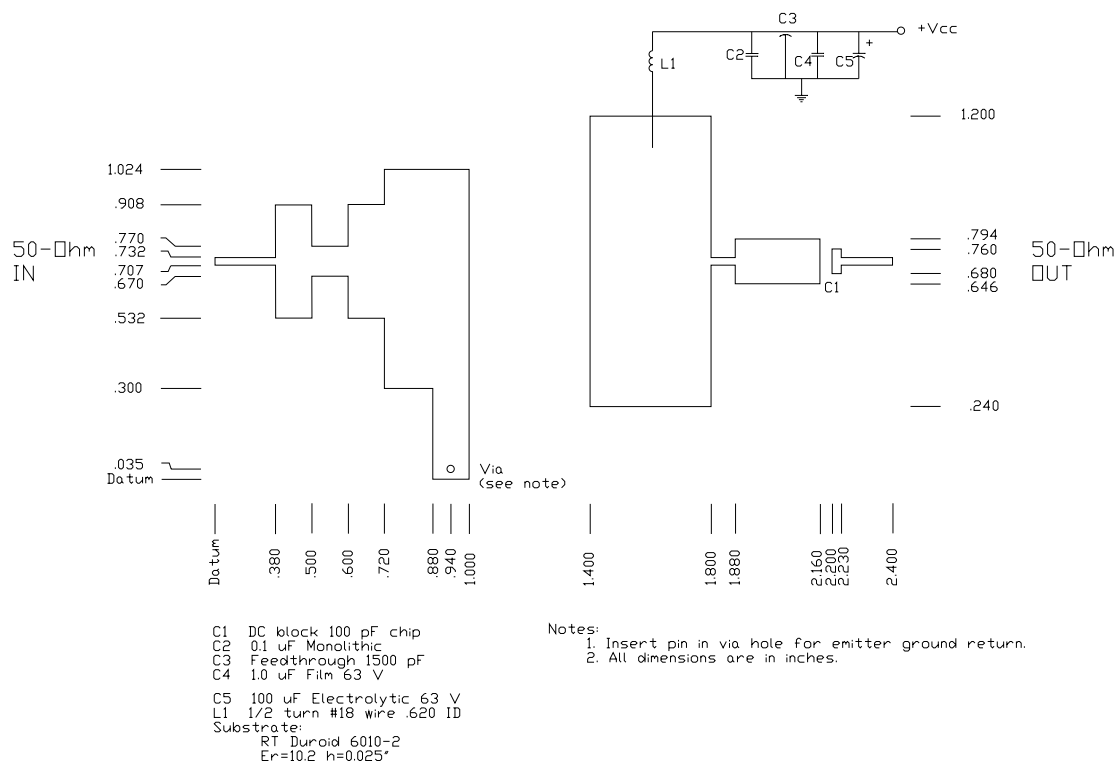
TYPICAL PERFORMANCE**POWER OUTPUT vs POWER INPUT****POWER OUTPUT vs FREQUENCY**

TEST CIRCUIT (1090 MHz)

Ref.: Dwg. No. C125410

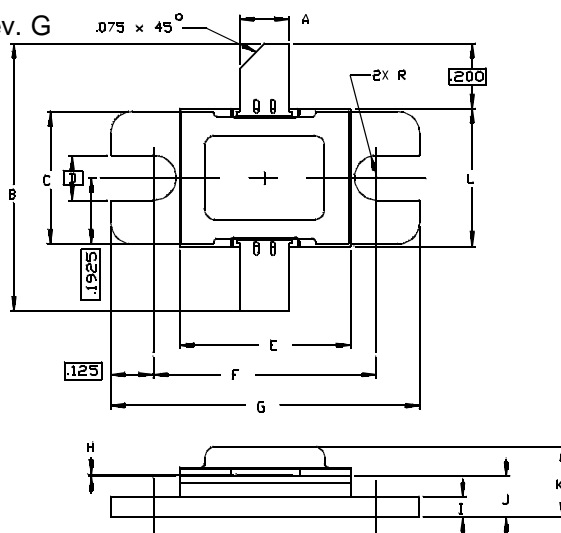


1030 MHz TYPICAL CIRCUIT



PACKAGE MECHANICAL DATA

Ref.: Dwg. No.12-0112 rev. G



SGS-THOMSON MICROELECTRONICS		
	MINIMUM Inches/mm	MAXIMUM Inches/mm
A	.145/3.68	.155/3.93
B	.750/19.05	
C	.380/9.65	.390/9.91
D	.130/3.30	
E	.495/12.57	.507/12.88
F	.640/16.26	.655/16.64
G	.890/22.61	.910/23.11
H	.002/0.05	.006/0.15
I	.055/1.40	.065/1.65
J	.115/2.92	.135/3.43
K		.230/5.84
L	.395/10.03	.407/10.34

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